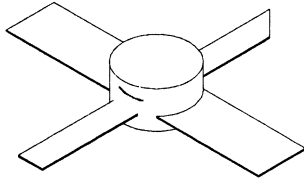


MS2361

75 Watts, 50 Volts, Class C
Avionics 1025 - 1150 MHz

GENERAL DESCRIPTION		
The MS2361 is a COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 1025-1150 MHz. The device has gold thin-film metallization for proven highest MTTF. The transistor includes input prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.		
ABSOLUTE MAXIMUM RATINGS		
Maximum Power Dissipation @ 25°C ²	250 Watts Pk	
Maximum Voltage and Current		
BVces	Collector to Emitter Voltage	65 Volts
BVebo	Emitter to Base Voltage	3.5 Volts
Ic	Collector Current	6.5 Amps Pk
Maximum Temperatures		
Storage Temperature		- 65 to + 150°C
Operating Junction Temperature		+ 200°C

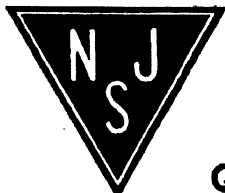
ELECTRICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P _{OUT}	Power Out	F = 1025-1150 MHz	75			W
P _{IN}	Power Input	V _{cc} = 50 Volts			13	W
P _G	Power Gain	PW = 10 μsec, DF = 1%	7.6	8.5		dB
η _c	Efficiency			40		%
VSWR ¹	Load Mismatch Tolerance	F = 1090 MHz			20:1	

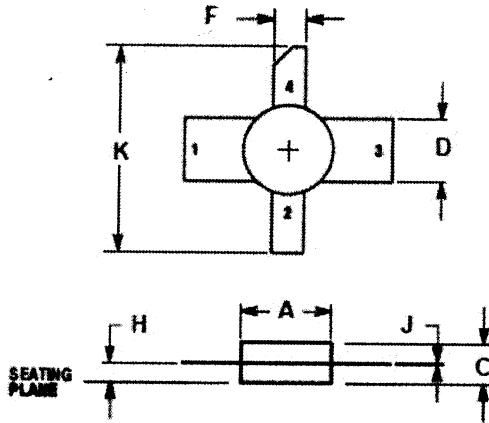
FUNCTIONAL CHARACTERISTICS @ 25°C

BVebo	Emitter to Base Breakdown	I _e = 5 mA	3.5			V
BVces	Collector to Emitter Breakdown	I _c = 15mA	65			V
H _{fe}	DC Current Gain	V _{ce} = 5V, I _c = 2.5 Adc	10	30		
C _{ob}	Output Capacitance	V _{cb} = 50 V, f = 1 MHz		12		pF
θ _{jc} ¹	Thermal Resistance				0.6	°C/W

Note 1: At rated pulse conditions



Quality Semi-Conductors



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.270	0.290	6.86	7.36
C	0.115	0.135	2.93	3.42
D	0.195	0.205	4.93	5.20
F	0.095	0.105	2.42	2.66
H	0.050	0.070	1.27	1.77
J	0.003	0.007	0.08	0.17
K	0.600	---	15.24	---

STYLE 1:

- PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR